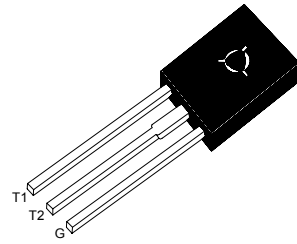


ST BT134T

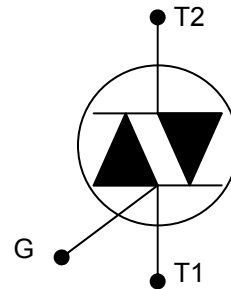
TRIAC

APPLICATIONS

- For use in high bidirectional transient and blocking voltage applications
- For high thermal cycling performance
- Typical application include motor control, industrial and domestic lighting, heating and static switching



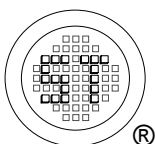
TO-126 Plastic Package



Absolute Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---|--------------|----------------------|------------------------|
| Repetitive Peak Off State Voltage | V_{DRM} | 600 ¹⁾ | V |
| RMS on State Current Full Sine Wave, $T_{mb} \leq 107\text{ }^{\circ}\text{C}$ | $I_{T(RMS)}$ | 4 | A |
| Non-Repetitive Peak on State Current Full Sine Wave, $T_J = 25\text{ }^{\circ}\text{C}$ Prior to Surge | I_{TSM} | 25 27 | A |
| I^2t for Fusing | I^2t | 3.1 | A^2s |
| Repetitive Rate of Rise of on State Current after Triggering $I_{TM} = 6\text{ A}$, $I_G = 0.2\text{ A}$, $dI_G/dt = 0.2\text{ A}/\mu\text{s}$ | dI_T/dt | 50 50 50 10 | $\text{A}/\mu\text{s}$ |
| Peak Gate Current | I_{GM} | 2 | A |
| Peak Gate Voltage | V_{GM} | 5 | V |
| Peak Gate Power | P_{GM} | 5 | W |
| Average Gate Power (Over any 20 ms period) | $P_{G(AV)}$ | 0.5 | W |
| Operating Junction Temperature | T_J | 125 | $^{\circ}\text{C}$ |
| Storage Temperature Range | T_{stg} | -40 to +150 | $^{\circ}\text{C}$ |

¹⁾ The rate of rise of current should not exceed $3\text{ A}/\mu\text{s}$



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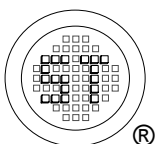
ST BT134T

Characteristics at $T_J = 25\text{ }^\circ\text{C}$

| Parameter | Symbol | Min. | Typ. | Max. | Unit |
|--|---------------|-----------|--------|----------|------------------|
| Gate Trigger Current at $V_D = 12\text{ V}$, $I_T = 0.1\text{ A}$ | I_{GT} | - | - | 35 | mA |
| T2+ G+ | | | | 35 | |
| T2+ G- | | | | 35 | |
| T2- G+ | | | | 70 | |
| Latching Current at $V_D = 12\text{ V}$, $I_{GT} = 0.1\text{ A}$ | I_L | - | - | 20 | mA |
| T2+ G+ | | | | 30 | |
| T2+ G- | | | | 20 | |
| T2- G+ | | | | 30 | |
| Holding Current at $V_D = 12\text{ V}$, $I_{GT} = 0.1\text{ A}$ | I_H | - | - | 15 | mA |
| On State Voltage at $I_T = 5\text{ A}$ | V_T | - | - | 1.7 | V |
| Gate Trigger Voltage at $V_D = 12\text{ V}$, $I_T = 0.1\text{ A}$ at $V_D = 400\text{ V}$, $I_T = 0.1\text{ A}$, $T_J = 125\text{ }^\circ\text{C}$ | V_{GT} | - 0.25 | - - | 1.5 - | V |
| Off State Leakage Current at $V_D = \text{max}$, $V_{DRM} = \text{max}$, $T_J = 125\text{ }^\circ\text{C}$ | I_D | - | - | 0.5 | mA |
| Critical Rate of Rise of Off State Voltage at $V_{DM} = 67\% V_{DRM} \text{ max}$, $T_J = 125\text{ }^\circ\text{C}$, exponential waveform, gate open circuit | dV_D/dt | 100 | 250 | - | V/ μs |
| Critical Rate of Change of Commutating Voltage at $V_{DM} = 400\text{ V}$, $T_J = 95\text{ }^\circ\text{C}$, $I_{T(RMS)} = 4\text{ A}$, $dI_{com}/dt = 1.8\text{ A/ms}$, gate open circuit | dV_{com}/dt | - | 50 | - | V/ μs |
| Gate Controlled Turn On Time at $I_{TM} = 6\text{ A}$, $V_D = V_{DRM} \text{ max}$, $I_G = 0.1\text{ A}$, $dI_G/dt = 5\text{ A}/\mu\text{s}$, | t_{gt} | - | 2 | - | μs |

Thermal Resistance

| Parameter | Symbol | Value | Unit |
|-------------------------------|----------------|------------|------|
| Junction to Mounting Base | $R_{th(j-mb)}$ | 3 | K/W |
| Full Cycle Half Cycle | | 3.7 | |
| Junction to Ambient (typical) | $R_{th(j-a)}$ | 100 (Typ.) | K/W |



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